

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (Currently Amended) A semiconductor polishing composition comprising:

fumed silica as abrasive grains, the fumed silica having a bulk density of 50 g/L or more and less than 100 g/L;

~~the semiconductor polishing composition being obtained by preparing a mixture of an acidic aqueous solution-solution; and fumed silica having a bulk density of 50 g/L or more and less than 100 g/L, and~~

~~an alkali aqueous solution; and so that pH of the mixture is in a range of 1 to 3 and pH of the alkali aqueous solution is in a range of 12 to 14, and adding the mixture to the alkali aqueous solution continuously or intermittently,~~

~~coarse particles of approximately 0.5 µm in diameter, the number of coarse particles being less than 140,000/0.5 ml, wherein the alkali aqueous solution contains at least one or two or more additives additive selected from a polishing accelerator, an oxidant, an organic acid, a complexing agent, a corrosion inhibitor and a surfactant.~~

2. (Original) The semiconductor polishing composition of claim 1, wherein a

content of the fumed silica is in a range of 10% by weight to 30% by weight based on a total amount of the composition.

- 3.-6. (Cancelled)

7. (Currently Amended) The semiconductor polishing composition of claim 1,
wherein alkali contained in the alkali aqueous solution ~~is~~includes at least one or two or more hydroxides~~hydroxide~~ selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.

8. (Cancelled)

9. (Currently Amended) The semiconductor polishing composition of claim 2,
wherein alkali contained in the alkali aqueous solution ~~is~~includes at least one or two or more hydroxides~~hydroxide~~ selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.

10.-11. (Cancelled)